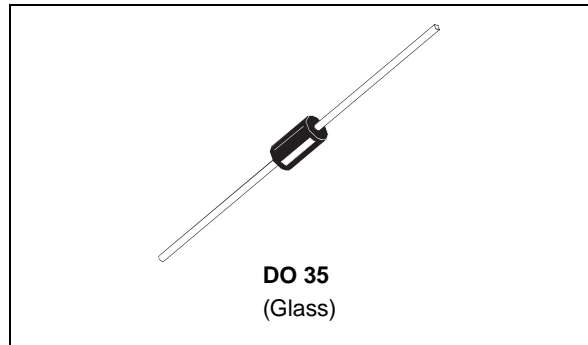


## SMALL SIGNAL SCHOTTKY DIODE

### DESCRIPTION

Metal to silicon junction diode featuring high breakdown, low turn-on voltage and ultrafast switching. Primarily intended for high level UHF/VHF detection and pulse application with broad dynamic range.



### ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	60	V
$I_F$	Forward Continuous Current*	$T_a = 25^\circ\text{C}$ 15	mA
$I_{FSM}$	Surge non Repetitive Forward Current*	$t_p \leq 1\text{s}$ 50	mA
$T_{stg}$ $T_j$	Storage and Junction Temperature Range	- 65 to 200 - 65 to 200	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering during 10s at 4mm from Case	230	$^\circ\text{C}$

### THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
$R_{th(j-a)}$	Junction-ambient*	400	$^\circ\text{C}/\text{W}$

### ELECTRICAL CHARACTERISTICS

#### STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$V_{BR}$	$T_{amb} = 25^\circ\text{C}$	$I_R = 10\mu\text{A}$	60			V
$V_F^{**}$	$T_{amb} = 25^\circ\text{C}$	$I_F = 1\text{mA}$			0.41	V
	$T_{amb} = 25^\circ\text{C}$	$I_F = 15\text{mA}$			1	
$I_R^{**}$	$T_{amb} = 25^\circ\text{C}$	$V_R = 50\text{V}$			0.2	$\mu\text{A}$

#### DYNAMIC CHARACTERISTICS

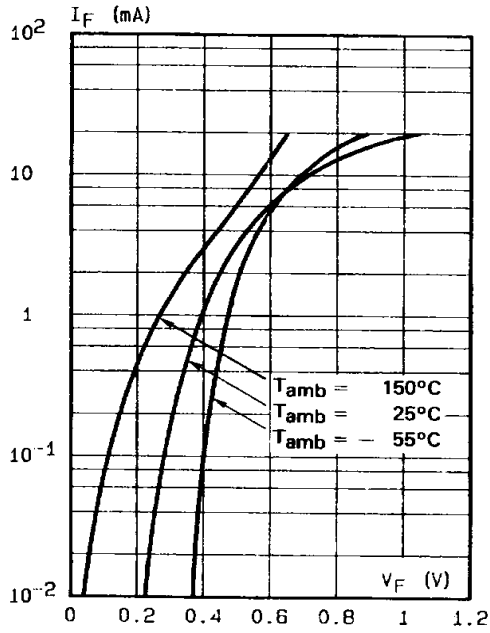
Symbol	Test Conditions			Min.	Typ.	Max.	Unit
C	$T_{amb} = 25^\circ\text{C}$	$V_R = 0\text{V}$	$f = 1\text{MHz}$			2.2	pF
$\tau$	$T_{amb} = 25^\circ\text{C}$	$I_F = 5\text{mA}$	Krakauer Method			100	ps

\* On infinite heatsink with 4mm lead length

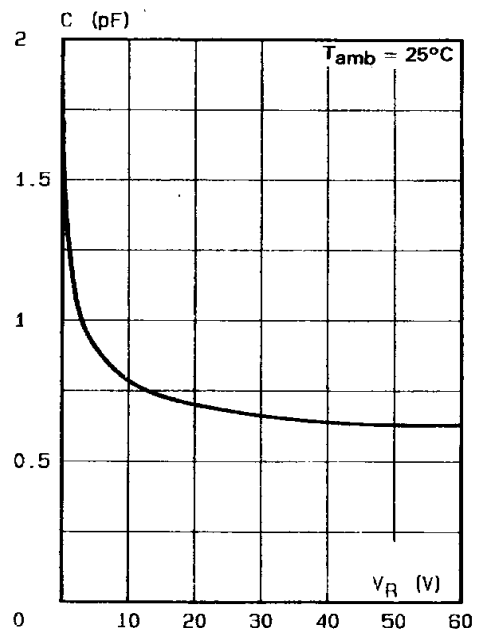
\*\* Pulse test:  $t_p \leq 300\mu\text{s}$   $\delta < 2\%$ .

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

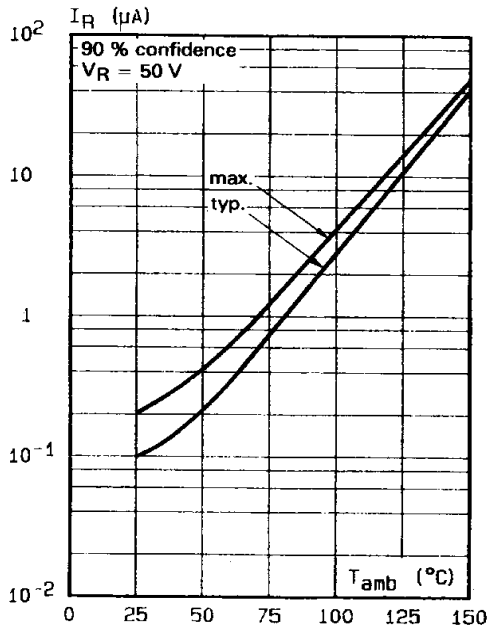
**Fig.1 :** Forward current versus forward voltage (typical values).



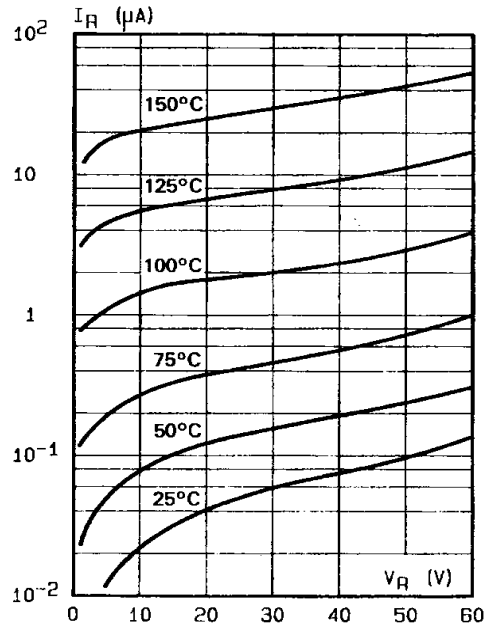
**Fig.2 :** Capacitance C versus reverse applied voltage  $V_R$  (typical values).



**Fig.3 :** Reverse current versus ambient temperature.

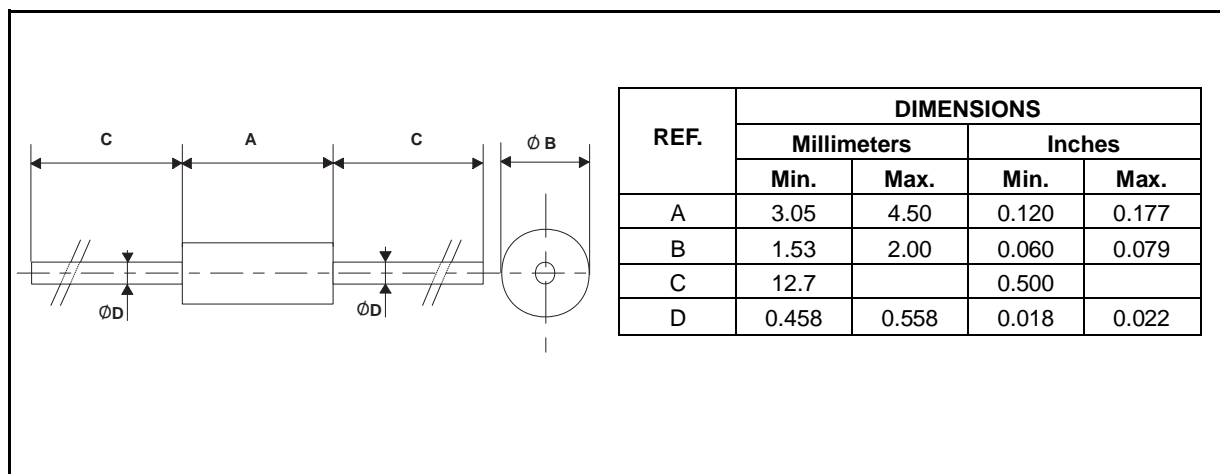


**Fig.4 :** Reverse current versus continuous reverse voltage (typical values).



## PACKAGE MECHANICAL DATA

DO 35 Glass



Cooling method : by convection and conduction

Marking: clear, ring at cathode end.

Weight: 0.15g

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